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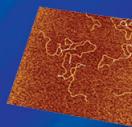
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This article was originally published without Fig. 1; Figure 2 appeared incorrectly in its place. The correct Fig. 1 and caption appear below. All online versions of the article have been corrected.

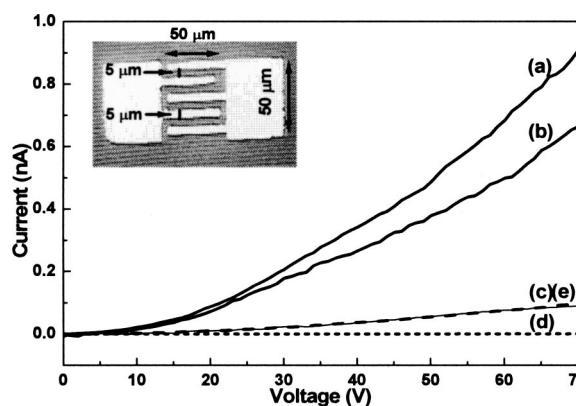


FIG. 1. Photocurrent of as-implanted BSO:Si⁺ MSM-PD at wavelength of: (a) 488 nm and (b) 514.5 nm under 1.5 mW illumination as compared to the dark current of MSM-PD on (c) as-implanted BSO:Si⁺, (d) unprocessed BSO glass, and (e) illuminated as-implanted BSO:Si⁺. The inset is the pattern of BSO:Si⁺ MSM-PD.

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